# UNISONIC TECHNOLOGIES CO., LTD

## 2SD879

#### NPN EPITAXIAL SILICON TRANSISTOR

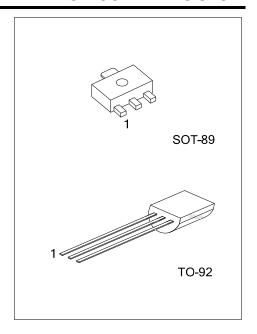
## 1.5V, 3V STROBE **APPLICATIONS**

#### DESCRIPTION

The UTC 2SD879 is a NPN epitaxial silicon transistor, designed for 1.5V and 3V strobe applications.

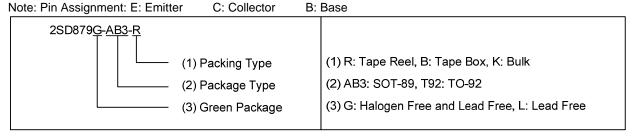
#### **FEATURES**

- \* In applications where two NiCd batteries are used to provide 2.4V, two 2SD879s are used.
- \* The charge time is approximately 1 second faster than that of germanium transistors.
- \* Less power dissipation because of I<sub>WO</sub> Collector-to-Emitter Voltage  $V_{\text{CE(SAT)}}$ , permitting more flashes of light to be emitted.
- \* Large current capacity and highly resistant to break-down.
- \* Excellent linearity of hFE in the region from low current to high current.

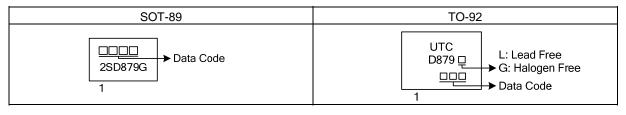


#### **ORDERING INFORMATION**

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
-	2SD879G-AB3-R	SOT-89	В	С	Е	Tape Reel	
2SD879L-T92-B	2SD879G-T92-B	TO-92	Е	С	В	Tape Box	
2SD879L-T92-K	2SD879G-T92-K	TO-92	E	С	В	Bulk	



#### **MARKING**



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#### ■ ABSOLUTE MAXIMUM RATING (T<sub>A</sub>=25°C ,unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	$V_{CBO}$	30	<b>&gt;</b>
Collector-Emitter Voltage	$V_{CEX}$	20	<b>&gt;</b>
Collector-Emitter Voltage	$V_{CEO}$	10	<b>&gt;</b>
Emitter-Base Voltage	$V_{EBO}$	6	<b>&gt;</b>
Collector Dissipation	P <sub>D</sub>	1	W
Collector Current (DC)	I <sub>C</sub>	3	Α
Collector Current (PULSE)	I <sub>CP</sub>	5	Α
Junction Temperature	TJ	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ <b>+</b> 150	°C

Notes: 1. Pulse Condition -> 100 ms single pulse

### ■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Voltage	$V_{CBO}$	I <sub>C</sub> =10uA, I <sub>E</sub> =0	30			V
Collector-Emitter Voltage	$V_{CEX}$	I <sub>C</sub> =1mA, V <sub>BE</sub> =3V	20			V
Collector-Emitter Voltage	$V_{CEO}$	I <sub>C</sub> =1mA, R <sub>BE</sub> =∞	10			V
Emitter-Base Voltage	$V_{EBO}$	I <sub>E</sub> =10uA, I <sub>C</sub> =0	6			V
Base-Emitter Voltage	$V_{BE(ON)}$	V <sub>CE</sub> =1V, I <sub>C</sub> =2A		0.83	1.5	V
Collector Cut-Off Current	I <sub>CBO</sub>	V <sub>CB</sub> =20V, I <sub>E</sub> =0			1	μΑ
Emitter Cut-Off Current	I <sub>EBO</sub>	$V_{EB}=4V$ , $I_{C}=0$			1	μΑ
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =2V, I <sub>C</sub> =3A (pulse)	140	210	400	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I <sub>C</sub> =3A, I <sub>B</sub> =60mA (pulse)		0.3	0.4	V
Current Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =50mA		200		MHz
Output Capacitance	C <sub>OB</sub>	V <sub>CB</sub> =10V, f=1MHz		30		pF

Pulse: 1mS

<sup>2.</sup> Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

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